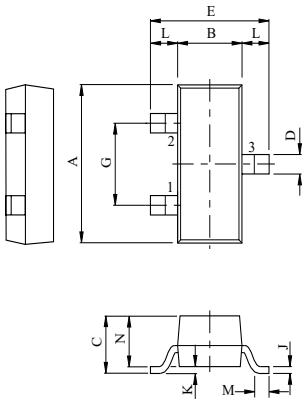
2N4403SC

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

· Complementary to the 2N4401SC



DIM	MILLIMETERS
A	2.90±0.1
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
J	0.10
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10

1. EMITTER
2. BASE
3. COLLECTOR

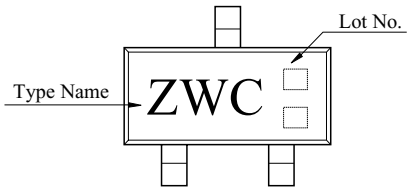
SOT-23(1)

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

Note : * Package Mounted On 99.5% Alumina 10×8×0.6㎜)

Marking

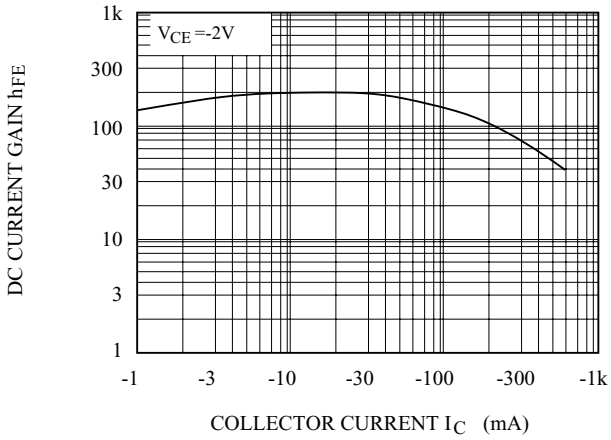


ELECTRICAL CHARACTERISTICS (Ta=25℃)

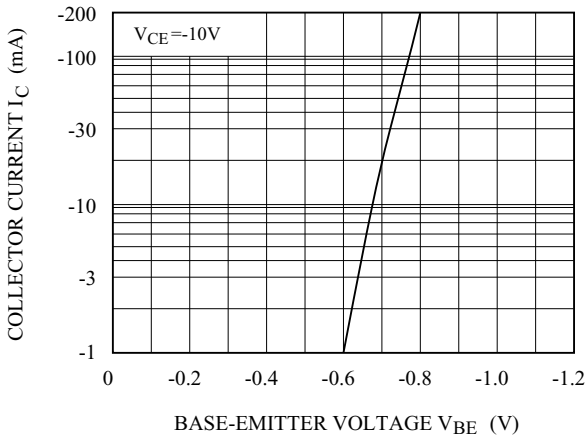
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CEX}	V_{CE}=-35V, V_{EB}=-0.4V	-	-	-50	nA
Collector Cut-off Current	I_{CBO}	V_{CB}=-40V, I_E=0	-	-	-20	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-3V, I_C=-10mA	-	-	-10	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100 μA, I_E=0	-40	-	-	V
Collector-Emitter Breakdown Voltage *	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-100 μA, I_C=0	-5	-	-	V
DC Current Gain *	h_{FE}	V_{CE}=-10V, I_C=-150mA	150	-	250	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-1.6	V
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-2.6	V
Transition Frequency	f_T	V_{CE}=-20V, I_C=-20mA f=100MHz	250	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	-	8.5	pF

* Pulse Test : Pulse Width≦300 μS, Duty Cycle≦2%.

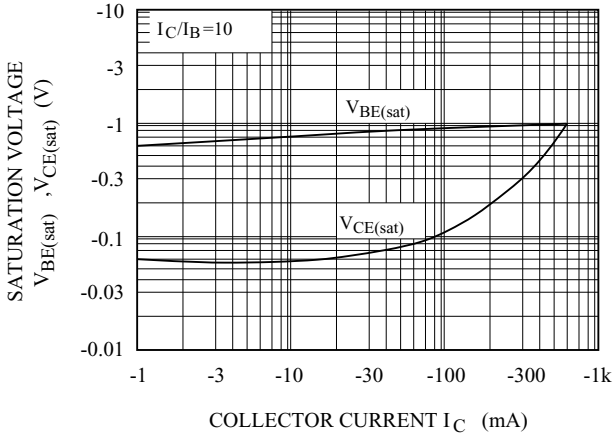
h_{FE} - I_C



I_C - V_{BE}



$V_{BE(sat)}$,$V_{CE(sat)}$ - I_C



C_{cb} - V_{CB}